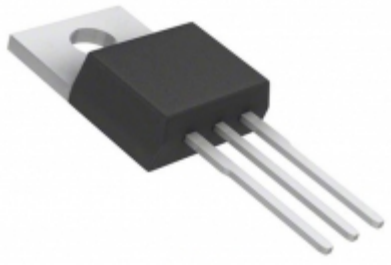


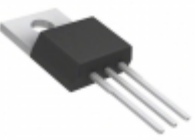
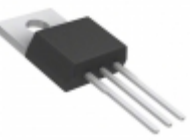



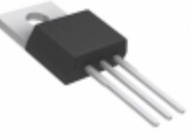
	<h2 style="color: red;">FQP6N60C</h2> <p>Hersteller-Teilenummer: FQP6N60C</p> <p>Hersteller / Marke: Fairchild/ON Semiconductor</p> <p>Teil der Beschreibung: MOSFET N-CH 600V 5.5A TO-220</p> <p>Datenblätter: 1.FQP6N60C.pdf 2.FQP6N60C.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 32303 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	FQP6N60C
Hersteller	Fairchild/ON Semiconductor
Beschreibung	MOSFET N-CH 600V 5.5A TO-220
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	32303 pcs Stock
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-220-3
Supplier Device-Gehäuse	TO-220-3
Verlustleistung (max)	125W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	600V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	5.5A (Tc)
Rds On (Max) @ Id, Vgs	2 Ohm @ 2.75A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	20nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	810pF @ 25V
Verpackung	Tube

FQP6N60C ist neu im Original, Suche FQP6N60C Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQP6N60C Fairchild/ON Semiconductor mit Garantie und Vertrauen.
Anfrage FQP6N60C: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQP6N60C_F080 AMI Semiconductor / ON Semiconductor MOSFET N-CH 600V 5.5A TO-220</p>	 <p>FQP6N50C AMI Semiconductor / ON Semiconductor MOSFET N-CH 500V 5.5A TO-220</p>	 <p>FQP6N60 Fairchild/ON Semiconductor MOSFET N-CH 600V 6.2A TO-220</p>	 <p>FQP6N70 AMI Semiconductor / ON Semiconductor MOSFET N-CH 700V 6.2A TO-220</p>
 <p>FQP6N70 Fairchild/ON Semiconductor MOSFET N-CH 700V 6.2A TO-220</p>	 <p>FQP6N60C_F080 Fairchild/ON Semiconductor MOSFET N-CH 600V 5.5A TO-220</p>	 <p>FQP6N60 AMI Semiconductor / ON Semiconductor MOSFET N-CH 600V 6.2A TO-220</p>	 <p>FQP6N60C AMI Semiconductor / ON Semiconductor MOSFET N-CH 600V 5.5A TO-220</p>

heiße Teile

Mehr

⊗ FQP50N06L	↔ FQP50N06L	⇒ FQP50N08	D FQP55N06	↔ FQP55N06
⊣ FQP55N10	⊗ FQP55N10	D FQP58N08	⇒ FQP58N08	↔ FQP5N20L
⊗ FQP5N20L	⊣ FQP5N50C	⊗ FQP5N50C	↔ FQP5N60C	↔ FQP5N60C
D FQP630TSTU	⊗ FQP630TSTU	⊣ FQP65N06	⊗ FQP65N06	↔ FQP6N40C
⇒ FQP6N40C	↔ FQP6N40CF	⊗ FQP6N40CF	⊣ FQP6N50C	↔ FQP6N50C
↔ FQP6N60C	⇒ FQP6N80C	D FQP6N80C	⊗ FQP6N90C	⊣ FQP6N90C
⊗ FQP70N03L	D FQP70N06	⇒ FQP70N06C	↔ FQP70N08	↔ FQP70N08
⊣ FQP70N10	⊗ FQP70N10	↔ FQP7N10L	⇒ FQP7N10L	↔ FQP7N20L
⊗ FQP7N20L	⊣ FQP7N60C	⊗ FQP7N65C	D FQP7N65C	↔ FQP7N80C
↔ FQP7N80C	⊗ FQP85N06	⊣ FQP85N06	⊗ FQP8N50C	↔ FQP8N60C

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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